



LM4040Q

AUTOMOTIVE COMPLIANT PRECISION MICROPOWER SHUNT VOLTAGE REFERENCES

Description

The LM4040Q is a family of bandgap circuits designed to achieve precision micropower voltage references of 2.5V, 3.0V, 3.3V, 4.096V, and 5.0V. The devices are available in 0.2% B-grade, 0.5% C-grade, and 1% D-grade initial tolerances.

The devices are available in small outline, SOT23 surface mount package, which is ideal for applications where space is at a premium. Excellent performance is maintained over the 60µA to 15mA operating current range with a typical temperature coefficient of only 20ppm/°C. The device is designed to be highly tolerant of capacitive loads that maintain excellent stability.

This device offers a pin-for-pin compatible alternative to the industry standard LM4040 voltage reference for automotive applications.

Features

Small Package: SOT23

No Output Capacitor Required

• Output Voltage Tolerance

LM4040BQ: ±0.2% at +25°C
 LM4040CQ: ±0.5% at +25°C

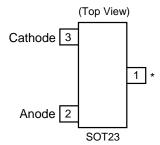
LM4040DQ: ±1% at +25°C

Low Output Noise

• 10Hz to 10kHz; 45μV_{RMS}

- Wide Operating Current Range of 60µA to 15mA
- Extended Temperature Range of -40°C to +125°C
- Low Temperature Coefficient of 100 ppm/°C (max)
- Green Molding in SOT23
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The LM4040Q is suitable for automotive applications requiring specific change control; this part is AEC-Q100 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities. https://www.diodes.com/quality/product-definitions/

Pin Assignments



* Pin 1 must be left floating or connected to pin 2

Applications

- Automotive Reference Voltage
- Data Acquisition Systems

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Absolute Maximum Ratings (Voltages to GND Unless Otherwise Stated)

	Parameter	Rating	Unit
Continuous	Reverse Current	20	mA
Continuous Forward Current		10	mA
Operating Junction Temperature		-40 to +150	°C
Storage Temperature		-55 to +150	°C
ESD Susce	ptibility		
HBM	Human Body Model	4	kV
CDM	Charged Device Model	1	kV

Caution:

Stresses greater than the Absolute Maximum Ratings specified above can cause permanent damage to the device. These are stress ratings only; functional operation of the device at conditions between maximum recommended operating conditions and absolute maximum ratings is not implied. Device reliability can be affected by exposure to absolute maximum rating conditions for extended periods of time.

Semiconductor devices are ESD sensitive and can be damaged by exposure to ESD events. Suitable ESD precautions should be taken when handling and transporting these devices.

Package Thermal Data

Package	θμα	P _{DIS} T _A = +25°C, T _J = +150°C
SOT23	380°C/W	330mW

Recommended Operating Conditions

Characteristic	Min	Max	Unit
Reverse Current	0.06	15	mA
Operating Ambient Temperature Range	-40	+125	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

LM4040-25Q

Symbol	Parameter	Conditions		Turn	B Limits	C Limits	D Limits	Unit
Symbol	Farameter	(Note 4)	TA	Тур	D LIIIIIS	CLIIIIIS	D LIIIIIS	Onit
	Reverse Breakdown Voltage	I _R = 100μA	+25°C	2.5	_	_	_	V
V_{REF}			+25°C		±5	±12	±25	
VREF	Reverse Breakdown Voltage Tolerance	$I_R = 100\mu A$	-40 to +85°C	_	±21	±29	±49	mV
			-40 to +125°C		±30	±38	±63	
			+25°C	45	60	60	65	
I _{RMIN}	Minimum Operating Current	_	-40 to +85°C	_	65	65	70	μΑ
			-40 to +125°C		68	68	73	
				±20	_	_	_	
$\Delta V_R/\Delta T$	Average Reverse Breakdown Voltage Temperature Coefficient	$I_R = 1mA$	-40 to +125°C	±15	±100	±100	±150	ppm/°C
		I _R = 100μA		±15	_	_	_	
		I _{RMIN} ≤ I _R ≤ 1mA	+25°C	0.3	0.8	0.8	1.0	
			-40 to +85°C		1.0	1.0	1.2	
ΔV _R /ΔI _R	Reverse Breakdown Voltage Change		-40 to +125°C		1.0	1.0	1.2	mV
Δνκ/Δικ	with Current	4 A - I -	+25°C	2.5	6.0	6.0	8.0	IIIV
		1mA ≤ I _R ≤ 15mA	-40 to +85°C		8.0	8.0	10.0	
		2 13IIIA	-40 to +125°C		8.0	8.0	10.0	
Z _R	Dynamic Output Impedance	I _R = 1mA, f = 120Hz, I _{AC} = 0.1I _R		0.3	0.8	0.9	1.1	Ω
en	Noise Voltage	I _R = 100μA, 10H	lz < f < 10kHz	35	_	_	_	μV _{RMS}
VR	Long Term Stability (Non-cumulative)	t = 1000Hrs, I _R :	= 100µA	120	_	_	_	ppm
VHYST	Thermal Hysteresis	$\Delta T = -40^{\circ}C$ to =	+125°C	0.08	_			%

Note: 4. Unless otherwise stated, voltages specified are relative to the Anode pin.



Electrical Characteristics ($@T_A = +25$ °C, unless otherwise specified.) (continued)

LM4040-30Q

0	D	Conditions		Turn	D. I. i	0.1.1	D 1 1 14 -	1114
Symbol	Parameter	(Note 4)	TA	Тур	B Limits	C Limits	D Limits	Unit
	Reverse Breakdown Voltage	$I_R = 100 \mu A$	+25°C	3.0	_	_	_	V
V_{REF}			+25°C		±6	±15	±30	
VREF	Reverse Breakdown Voltage Tolerance	$I_R = 100 \mu A$	-40 to +85°C	_	±26	±34	±59	mV
			-40 to +125°C		±36	±45	±75	
			+25°C	47	62	62	67	
IRMIN	Minimum Operating Current	_	-40 to +85°C		67	67	72	μΑ
			-40 to +125°C		70	70	75	
		$I_R = 10mA$		±20	_	_	_	
$\Delta V_R/\Delta T$	Average Reverse Breakdown Voltage Temperature Coefficient	$I_R = 1mA$	-40 to +125°C	±15	±100	±100	±150	ppm/°C
	Temperature Goemelent	I _R = 100μA		±15	_	_	_	
			+25°C	0.4	0.8	0.8	1.0	
		I _{RMIN} ≤ I _R ≤ 1mA	-40 to +85°C		1.1	1.1	1.3	mV
ΔV _R /ΔI _R	Reverse Breakdown Voltage Change		-40 to +125°C	_	1.1	1.1	1.3	
Δν κ/Δικ	with Current	4 4 1	+25°C	2.7	6.0	6.0	8.0	IIIV
		1mA ≤ I _R ≤ 15mA	-40 to +85°C		9.0	9.0	11.0	
		2 13IIIA	-40 to +125°C	_	9.0	9.0	11.0	
Z _R	Dynamic Output Impedance	I _R = 1mA, f = 120Hz, I _{AC} = 0.1I _R		0.4	0.9	0.9	1.2	Ω
en	Noise Voltage	I _R = 100μA, 10Hz < f < 10kHz		35	_	_	_	μV _{RMS}
V _R	Long Term Stability (Non-cumulative)	t = 1000Hrs, I _R = 100μA		120	_	_	_	ppm
VHYST	Thermal Hysteresis	$\Delta T = -40^{\circ} C \text{ to} = +125^{\circ} C$		0.08	_	_	_	%

LM4040-33Q

Cumb al	Donomoton	Conditions		Turn	Dimite	011:11-	D. I. Sandika	Unit
Symbol	Parameter	(Note 4)	TA	Тур	B Limits	C Limits	D Limits	Unit
	Reverse Breakdown Voltage	$I_R = 100 \mu A$	+25°C	3.3	_	_	_	V
VREF			+25°C		±6.6	±16.5	±33	
VKEF	Reverse Breakdown Voltage Tolerance	$I_R = 100\mu A$	-40 to +85°C	_	±28	±38	±65	mV
			-40 to +125°C		±40	±50	±83	
			+25°C	47	62	62	67	
I _{RMIN}	Minimum Operating Current	_	-40 to +85°C		67	67	72	μΑ
			-40 to +125°C		70	70	75	
	ΔV _R /ΔT Average Reverse Breakdown Voltage Temperature Coefficient	$I_R = 10mA$		±20	_	_	-	
$\Delta V_R/\Delta T$		$I_R = 1mA$	-40 to +125°C	±15	±100	±100	±150	ppm/°C
		$I_R = 100 \mu A$		±15	_	_	_	
			+25°C	0.4	0.8	0.8	1	
		I _{RMIN} ≤ I _R ≤ 1mA	-40 to +85°C		1.1	1.1	1.3	
$\Delta V_R/\Delta I_R$	Reverse Breakdown Voltage Change		-40 to +125°C] _	1.1	1.1	1.3	mV
Δν Κ/ΔΙΚ	with Current		+25°C	2.7	6	6	8	IIIV
		1mA ≤ I _R ≤ 15mA	-40 to +85°C		9.0	9	11	
		2 ISIIIA	-40 to +125°C		9.0	9	11	
Z_{R}	Dynamic Output Impedance	I _R = 1mA, f = 120Hz, I _{AC} = 0.1I _R		0.4	0.9	0.9	1.2	Ω
e n	Noise Voltage	I _R = 100µA, 10Hz < f < 10kHz		35				μVRMS
V _R	Long Term Stability (Non-cumulative)	t = 1000Hrs, I _R = 100µA		120		_	_	ppm
V _{HYST}	Thermal Hysteresis	$\Delta T = -40$ °C to = +125°C		0.08			_	%

Note: 4. Unless otherwise stated, voltages specified are relative to the Anode pin.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.) (continued)

LM4040-41Q

Company of	Danamatan	Conditions		T	Dimite	Climita	Dimita	Unit	
Symbol	Parameter	(Note 4)	TA	Тур	B Limits	C Limits	D Limits	Onit	
	Reverse Breakdown Voltage	$I_R = 100 \mu A$	+25°C	4.096	_	_	_	V	
V_{REF}			+25°C		±8.2	±20	±41		
VKEF	Reverse Breakdown Voltage Tolerance	$I_R = 100 \mu A$	-40 to +85°C	_	±35	±47	±81	mV	
			-40 to +125°C		±49	±60	±102		
			+25°C	50	83	83	83		
I _{RMIN}	Minimum Operating Current	_	-40 to +85°C		88	88	88	μΑ	
			-40 to +125°C		88	88	88		
	Average Reverse Breakdown Voltage Temperature Coefficient	$I_R = 10mA$		±30	_	_	_	ppm/°C	
$\Delta V_R/\Delta T$		I _R = 1mA	-40 to +125°C	±20	±100	±100	±150		
	Temperature docinicient	I _R = 100μA		±20	_	_	_		
			+25°C	0.5	0.9	0.9	1.2		
		I _{RMIN} ≤ I _R ≤ 1mA	-40 to +85°C		1.2	1.2	1.5	mV	
A\/-/AI-	Reverse Breakdown Voltage Change		-40 to +125°C		1.2	1.2	1.5		
$\Delta V_R/\Delta I_R$	With Current	4 4 1	+25°C	3	7	7	9	IIIV	
		1mA ≤ I _R ≤ 15mA	-40 to +85°C		10	10	13		
		13IIIA	-40 to +125°C		10	10	13		
ZR	Dynamic Output Impedance	I _R = 1mA, f = 120Hz, I _{AC} = 0.1I _R		0.5	1	1	1.3	Ω	
en	Noise Voltage	I _R = 100μA, 10Hz < f < 10kHz		64	_	_	_	μV _{RMS}	
V_R	Long Term Stability (Non-cumulative)	t = 1000Hrs, I _R = 100µA		120	_	_	_	ppm	
VHYST	Thermal Hysteresis	ΔT = -40°C to =	= +125°C	0.08	80	_	_	%	

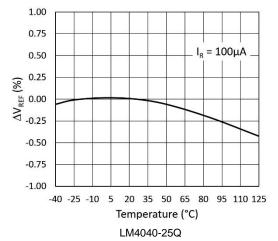
LM4040-50Q

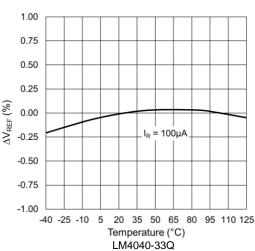
Comple al	Domonoston	Conditions		T	B Limits	C I imita	Dimita	Unit	
Symbol	Parameter	(Note 4)	TA	Тур	D LIIIIIIS	C Limits	D Limits	Onit	
	Reverse Breakdown Voltage	I _R = 100μA	+25°C	5.0	_	_	_	V	
V_{REF}			+25°C		±10	±25	±50		
VKEF	Reverse Breakdown Voltage Tolerance	$I_R = 100 \mu A$	-40 to +85°C	_	±43	±58	±99	mV	
			-40 to +125°C		±60	±75	±125		
			+25°C	54	74	74	79		
IRMIN	Minimum Operating Current	_	-40 to +85°C		80	80	85	μΑ	
			-40 to +125°C		83	83	88		
				±30	_	_	_		
$\Delta V_R/\Delta T$	Average Reverse Breakdown Voltage Temperature Coefficient	$I_R = 1mA$	-40 to +125°C	±20	±100	0 ±100 ±150	±150	ppm/°C	
	Temperature desineria	I _R = 100μA		±20	_	_	_		
		LRMIN ≤ IR +25°C -40 to +85°C verse Breakdown Voltage +25°C -40 to +85°C verse Breakdown Voltage +25°C -40 to +125°C verse Breakdown Voltage +25°C verse Breakdown Voltage +25°C	+25°C	0.5	1.0	1.0	1.3		
			-40 to +85°C		1.4	1.4	1.8		
ΔV _R /ΔI _R	Reverse Breakdown Voltage		-40 to +125°C	_	1.4	1.4	1.8	mV	
Δν Κ/ΔΙΚ	Change With Current	4 4 1	+25°C	3.5	8.0	8.0	10.0	IIIV	
		1mA ≤ I _R ≤ 15mA	-40 to +85°C		12.0	12.0	15.0		
		≥ ISIIIA	-40 to +125°C	_	12.0	12.0	15.0		
Z _R	Dynamic Output Impedance	I _R = 1mA, f = 120Hz, I _{AC} = 0.1I _R		0.5	1.1	1.1	1.5	Ω	
en	Noise Voltage	$I_R = 100 \mu A, 10I$	Hz < f < 10kHz	80			_	μVRMS	
VR	Long Term Stability (Non-cumulative)	t = 1000Hrs, I _R	t = 1000Hrs, I _R = 100μA		_	_	_	ppm	
VHYST	Thermal Hysteresis	$\Delta T = -40^{\circ}C$ to =	$\Delta T = -40^{\circ}C \text{ to} = +125^{\circ}C$		_	_	_	%	

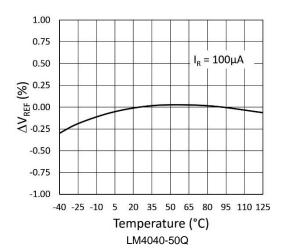
Note: 4. Unless otherwise stated, voltages specified are relative to the Anode pin.

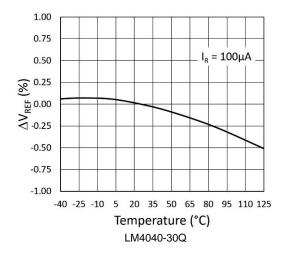


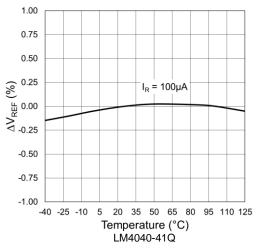
Typical Characteristics - Reference Voltage Temperature Coefficient at 100μA





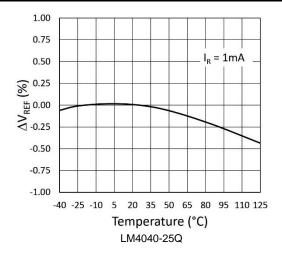


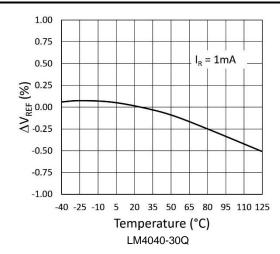


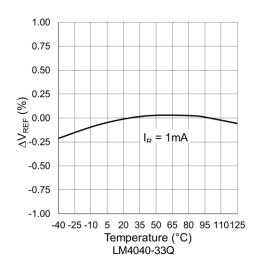


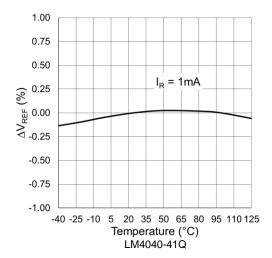


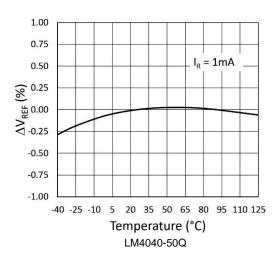
Typical Characteristics - Reference Voltage Temperature Coefficient at 1mA





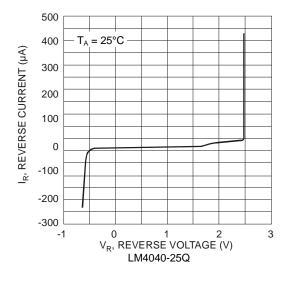


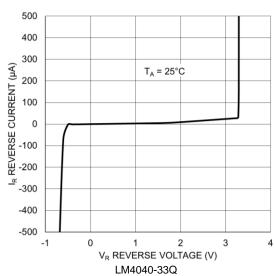


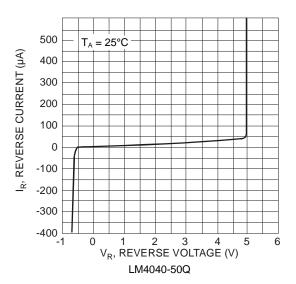


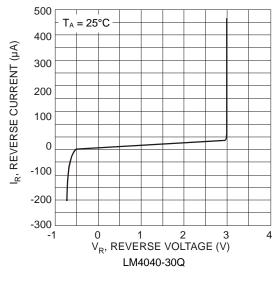


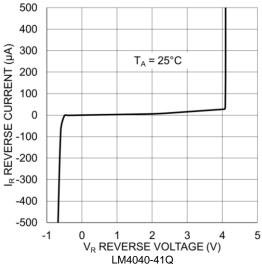
Typical Characteristics - Reverse Characteristics





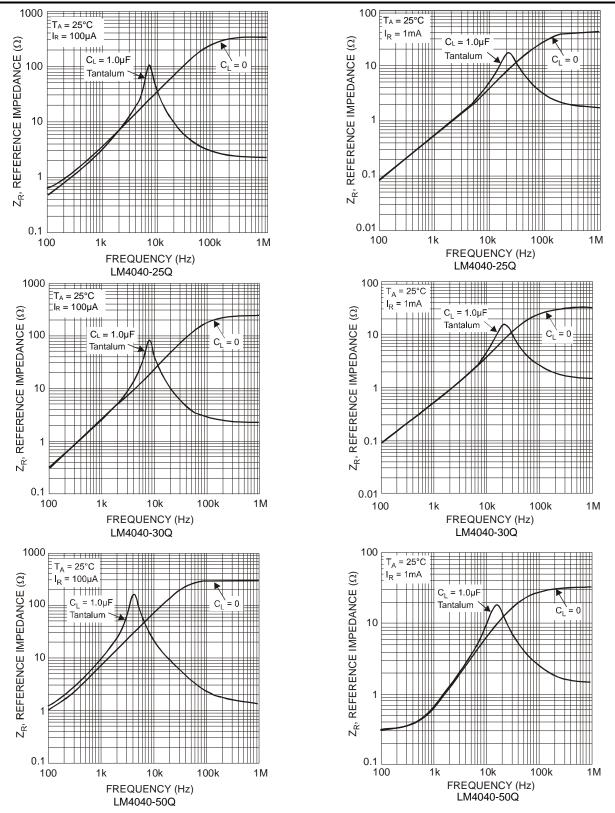






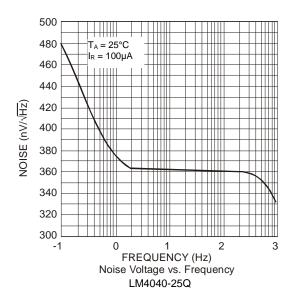


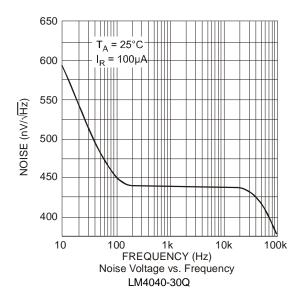
Typical Characteristics – LM4040Q Reference Impedance

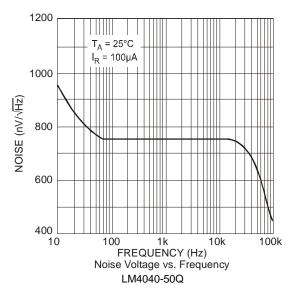




Typical Characteristics – LM4040Q Noise Characteristics

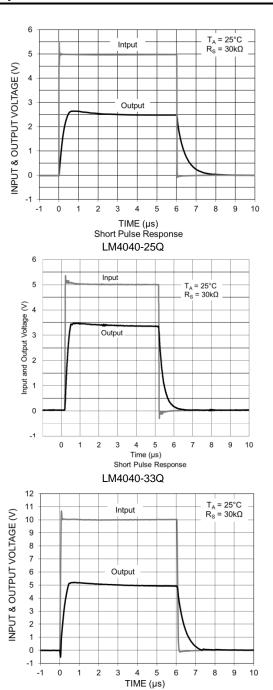




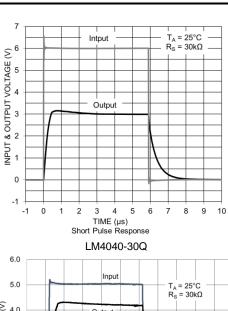


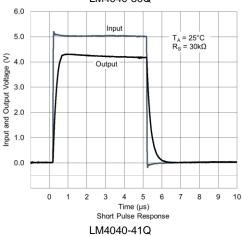


Start Up Characteristics - LM4040Q Short Pulse



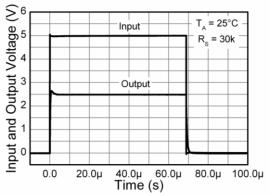
Short Pulse Response LM4040-50Q



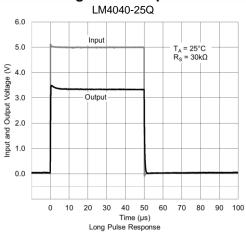


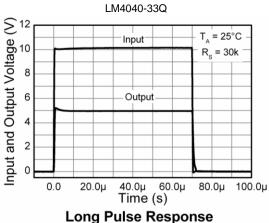


Start Up Characteristics - LM4040Q Long Pulse

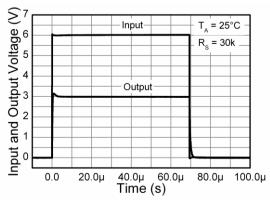


Long Pulse Response

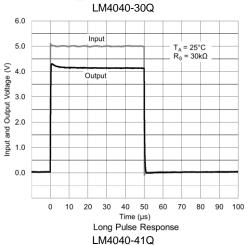




LM4040-50Q



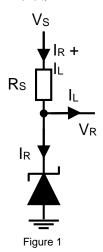
Long Pulse Response





Application Information

In a conventional shunt regulator application (Figure 1), an external series resistor (Rs) is connected between the supply voltage, Vs, and the LM4040Q.



Rs determines the current that flows through the load (I_L) and the LM4040Q (I_R). Because load current and supply voltage can vary, Rs should be small enough to supply at least the minimum acceptable I_R to the LM4040Q even when the supply voltage is at its minimum and the load current is at its maximum value. When the supply voltage is at its maximum and I_L is at its minimum, Rs should be large enough so the current flowing through the LM4040Q is less than 15mA.

 R_S is determined by the supply voltage, (V_S), the load and operating current, (I_L and I_R), and the LM4040Q's reverse breakdown voltage, V_R .

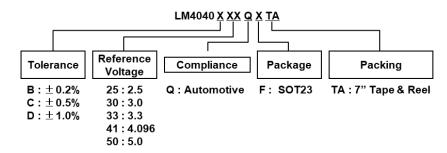
$$R_S = \frac{V_S - V_R}{I_L + I_R}$$

Printed Circuit Board Layout Considerations

LM4040Q devices in the SOT23 package have the die attached to pin 1, which results in an electrical contact between pin 2 and pin 3. Therefore, pin 1 of the SOT23 package must be left floating or connected to pin 2.



Ordering Information



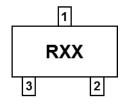
	25°€	Voltage	Package	Package	Identification	Packing: 7	" Tape and Re	el (Note 7)	Compliance
Order Code	Tol	(V)	(Note 5)	Code	Code	Quantity	Tape Width	Part Number Suffix	(Note 6)
LM4040B25QFTA		2.5	SOT23	F	R2B	3000	8mm	TA	Automotive
LM4040B30QFTA		3.0	SOT23	F	R3B	3000	8mm	TA	Automotive
LM4040B33QFTA	0.2%	3.3	SOT23	F	3B3Q	3000	8mm	TA	Automotive
LM4040B41QFTA		4.096	SOT23	F	4B1Q	3000	8mm	TA	Automotive
LM4040B50QFTA		5.0	SOT23	F	R5B	3000	8mm	TA	Automotive
LM4040C25QFTA		2.5	SOT23	F	R2C	3000	8mm	TA	Automotive
LM4040C30QFTA		3.0	SOT23	F	R3C	3000	8mm	TA	Automotive
LM4040C33QFTA	0.5%	3.3	SOT23	F	3C3Q	3000	8mm	TA	Automotive
LM4040C41QFTA		4.096	SOT23	F	4C1Q	3000	8mm	TA	Automotive
LM4040C50QFTA		5.0	SOT23	F	R5C	3000	8mm	TA	Automotive
LM4040D25QFTA		2.5	SOT23	F	R2D	3000	8mm	TA	Automotive
LM4040D30QFTA		3.0	SOT23	F	R3D	3000	8mm	TA	Automotive
LM4040D33QFTA	1%	3.3	SOT23	F	3D3Q	3000	8mm	TA	Automotive
LM4040D41QFTA		4.096	SOT23	F	4D1Q	3000	8mm	TA	Automotive
LM4040D50QFTA		5.0	SOT23	F	R5D	3000	8mm	TA	Automotive

5. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/package-outlines.html. 6. LM4040Q is classified as "Automotive Compliant" and supports PPAP documentation. See LM4040 datasheet for commercial qualified versions.

7. See https://www.diodes.com/assets/Packaging-Support-Docs/ap02007.pdf for tape and reel information.

Marking Information

LM4040-25Q, LM4040-30Q, LM4040-50Q



RXX: Identification Code

LM4040-33Q, LM4040-41Q

(Top View)

3 XXXQ <u>Y W X</u> XXXQ: Identification code

Y: Year: 0~9

W: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

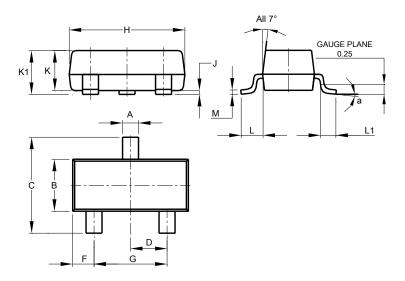
52 and 53 week X: Internal code



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

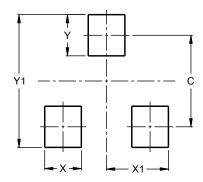


	SOT23								
Dim	Min	Max	Тур						
Α	0.37	0.51	0.40						
В	1.20	1.40	1.30						
С	2.30	2.50	2.40						
D	0.89	1.03	0.915						
F	0.45	0.60	0.535						
G	1.78	2.05	1.83						
Н	2.80	3.00	2.90						
J	0.013	0.10	0.05						
K	0.890	1.00	0.975						
K1	0.903	1.10	1.025						
L	0.45	0.61	0.55						
L1	0.25	0.55	0.40						
M	0.085	0.150	0.110						
а	0°	8°							
All	Dimens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

Note: The suggested land pattern dimensions have been provided for reference only, as actual pad layouts may vary depending on application. These dimensions may be modified based on user equipment capability or fabrication criteria. A more robust pattern may be desired for wave soldering and is calculated by adding 0.2 mm to the 'Z' dimension. For further information, please reference document IPC-7351A, Naming Convention for Standard SMT Land Patterns, and for International grid details, please see document IEC, Publication 97.



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KA431SLMF2TF KA431SMF2TF KA431SMFTF LM4041C12ILPR LM4120AIM5-2.5/NOP LM431SCCMFX LM285BXMX-1.2/NOPB

LM385BM-2.5/NOPB LM4040BIM3-4.1 LM4040CIM3-10.0 LM4040CIM3X-2.0/NOPB LM4041BSD-122GT3 LM4041QDIM3-ADJ/NO

LM4050QAEM3X4.1/NOPB LM4051BIM3-ADJ/NOPB LM4051CIM3X-1.2/NOPB LM4132DMF-1.8/NOPB LM4132EMF-2.0/NOPB

LM4140CCMX-1.2/NOPB LM431CIM LM385M-2.5/NOPB LM4030AMF-4.096/NOPB LM4040D30ILPR LM4051CIM3X-ADJ/NOPB

AP432YG-13 AS431ANTR-G1 AS431BZTR-E1 AP431IBNTR-G1 AS431ARTR-G1 AS431BNTR-G1 TL431AIZ AZ431AN-ATRG1

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